Thin Solid Films, 193/194 (1990) xxiii–xxvii

Contents

Amorphous materials and devices

Properties of, and effusion experiments on, deuterated, fluorinated amorphous silicon 565
R. Weil and A. Busso (Haifa, Israel) and W. Beyer (Jülich, F.R.G.)

Computer modelling of the diffusion mechanisms of fluorine in amorphous silicon 571
A. Silverman, J. Adler and R. Weil (Haifa, Israel)

Annealing of "intrinsic" and photo-induced defects in hydrogenated amorphous silicon 577
G. N. Parsons, C. Wang and G. Lucovsky (Raleigh, NC, U.S.A.)

Ion implantation effects in laser-deposited amorphous carbon films 588
A. P. Malshe, S. M. Chaudhari, S. M. Kanetkar, S. B. Ogale and S. T. Kshirsagar (Pune, India)

Oxides for device applications

Plasma-assisted chemical vapor deposition and characterization of high quality silicon oxide films 595
S. V. Nguyen, D. Dobuzinsky, D. Dopp, R. Gleason, M. Gibson and S. Fridmann (Essex Junction, VT, U.S.A.)

Real-time studies of gallium arsenide anodic oxidation 610
C. T. Lenczycki and V. A. Burrows (Tempe, AZ, U.S.A.)

Silicon oxide films deposited by excimer laser chemical vapour deposition . . 619
T. Szorényi, P. González, M. D. Fernández, J. Pou, B. León and M. Pérez-Amor (Vigo, Spain)

Plasma oxide growth on silicon and titanium disilicide 627
R. Pérez-Casero, J. Perrière and J. P. Enard (Paris, France), J. M. Martínez-Duart and A. Climent (Madrid, Spain)

Low temperature SiO_2 films 638
C. Falcony, A. Ortiz, S. Lopez, J. C. Alonso and S. Muhl (Mexico City, Mexico)

Oxide and oxy-nitride thin films

Formation and diffusion properties of oxide films on metals and on nitride coatings studied with Auger electron spectroscopy and X-ray photoelectron spectroscopy 648
S. Hofmann (Stuttgart, F.R.G.)

Oxidation of silicon (Oxy)nitride and nitridation of silicon dioxide: manifestations of the same chemical reaction system? 665
F. H. P. M. Habraken (Utrecht, The Netherlands) and A. E. T. Kuiper (Eindhoven, The Netherlands)

Investigations of the barrier layer of porous anodic coatings on aluminium . . 675
Ž. Bogdanov, N. Popović, M. Milić and T. Nenadović (Belgrade, Yugoslavia)

Study of aluminium oxide films formed by plasma anodization 683
P. S. Pawar, S. V. Gogawale, D. C. Kothari, A. M. Narsale, P. D. Prabhawalkar and P. M. Raole (Bombay, India)

Applications of oxides and optoelectric films

Structural and optical properties of zirconia thin films 690
M. G. Krishna, K. N. Rao and S. Mohan (Bangalore, India)

Transparent, conducting oxides and optical coatings

Reaction kinetics of the formation of indium tin oxide films grown by spray pyrolysis 696
V. Vasu and A. Subrahmanyam (Madras, India)

Optical and electrical properties of SnO_x thin films made by reactive r.f. magnetron sputtering 704
B. Stjerna and C. G. Granqvist (Gothenberg, Sweden)

Optical and electrical properties of Ga_2O_3-doped ZnO films prepared by r.f. sputtering. 712
B. H. Choi and H. B. Im (Seoul, South Korea), J. S. Song and K. H. Yoon (Daejeon, South Korea)

Preparations of ZnO:Al transparent conducting films by d.c. magnetron sputtering. 721
T. Minami, K. Oohashi and S. Takata (Ishikawa, Japan), T. Mouri and N. Ogawa (Yamaguchi, Japan)

Optical coatings and optoelectric devices

Window coatings for the future 730
C. G. Granqvist (Gothenburg, Sweden)

Optical bistability in multicavity ZnSe interference filters at 514 nm. 742
H. Zorc (Zagreb, Yugoslavia)

Colour of dielectric–conductive double-layer films deposited by dry-coating processes 748
S. Miyajima and M. Hashimoto (Kawasaki, Japan)

Solar cells and materials

Recent development in thin film solar cells 757
N. G. Dhere (Rio de Janeiro, Brazil)

Study of the interface properties of $CuInSe_2$ single-crystal heterojunctions and Schottky barriers 769
F. Abou-Elfotouh, R. J. Matson, A. M. Bakry and L. L. Kazmerski (Golden, CO, U.S.A.)

Photovoltaic properties of n-CdS/p-Cu_2Te thin film heterojunctions 777
O. M. Hussain, B. S. Naidu and P. J. Reddy (Tirupati, India)

Multilayer thin films, including mirrors

Ion-beam-assisted deposition of Ni/C multilayer X-ray mirrors 782
E. J. Puik and M. J. van der Wiel (Nieuwegein, The Netherlands), J. Verhoeven and H. Zeijlemaker (Amsterdam, The Netherlands)

Preparation of multilayered film structures by laser arcs 788
H.-J. Scheibe and W. Pompe (Dresden, G.D.R.), P. Siemroth (Berlin, G.D.R.), B. Buecken, D. Schulze and R. Wilberg (Dresden, G.D.R.)

Microstructure of Au/Nb multilayers 799
A. F. Jankowski and P. L. Perry (Livermore, CA, U.S.A.)

Characterization of as-prepared and oxidized Hf/Fe multilayer films 807
Y. Takagi (Kawasaki, Japan), B. S. Chao, A. R. Chan and D. A. Pawlik (Troy, MI, U.S.A.)

Growth, structural characterization and properties of hard and wear-protective layered materials 818
J.-E. Sundgren, J. Birch, G. Håkansson, L. Hultman and U. Helmersson (Linköping, Sweden)

High temperature superconductors and applications

The effects of concurrent oxygen ion bombardment on ion beam sputtered $Y_1Ba_2Cu_3O_x$ thin films 832
J. P. Doyle, R. A. Roy and J. J. Cuomo (Yorktown Heights, NY, U.S.A.)

Growth of Y–Ba–Cu–O superconducting thin films by ultrasonic spray pyrolysis 841
S. P. S. Arya and H. E. Hintermann (Neuchâtel, Switzerland)

Post-deposition treatments of plasma-sprayed YBaCuO coatings deposited on nickel 847
D. Dubé, P. Lambert, B. Arsenault and B. Champagne (Boucherville, Que., Canada)

Magnetic films, applications and measurements

Improved crystal texture control for rare earth–transition metal magnetic films sputtered in Ar–Xe gas mixtures 857
F. J. Cadieu, H. Hegde and K. Chen (Flushing, NY, U.S.A.)

Transverse Kerr magneto-optic effects: magnetic film on a magnetic substrate 866
V. W. Biricik (Palos Verdes Pensinsula, CA, U.S.A.)

Interlayer coupling in [3d ferromagnetic/non-magnetic]$_n$ multilayers 877
C. Lacroix, B. Dieny, J. P. Gavigan and D. Givord (Grenoble, France)

Multichip modules for high performance computer applications 886
J. T. Pan, C. Hilbert and B. Weigler (Austin, TX, U.S.A.)

High field electronic conduction processes in copper phthalocyanine thin films using lead and gold electrode combinations. 895
R. D. Gould and A. K. Hassan (Keele, U.K.)

Thin and thick film sensors

The pyroelectric thin film sensor: a novel tool for the analysis of thin films . . 905
H. J. Coufal (San José, CA, U.S.A.)

Preparation and characterization of reactively sputtered SiC_xN_y films 917
S. Komatsu, Y. Hirohata, S. Fukuda, T. Hino and T. Yamashina (Sapporo, Japan), T. Hata and K. Kusakabe (Osaka-fu, Japan)

Thin film temperature heat fluxmeters 924
J. C. Godefroy, M. Cléry, C. Gageant, D. François and Y. Servouze (Châtillon, France)

Hall effect measurements in SnO_x film sensors exposed to reducing and oxidizing gases 935
R. Sanjinés (Lausanne, Switzerland), V. Demarne (Neuchâtel, Switzerland) and F. Lévy (Lausanne, Switzerland)

Poster session on aspects of thin films

Feasibility study of the chemical vapour transport of ternary compound semiconductor thin films. 943
K. Balakrishnan, B. Vengatesan, N. Kanniah and P. Ramasamy (Madras, India)

Surface roughness of aluminum thin films deposited by effusive and ionized cluster beams 951
L. L. Levenson (Colorado Springs, CO, U.S.A.), A. Yahashi, H. Usui and I. Yamada (Kyoto, Japan)

Reactions at the aluminum oxide–ferrite interface 959
Y.-S. Chaug and N. Roy (Louisville, CO, U.S.A.)

Dual microwave–r.f. plasma deposition of functional coatings 965
J. E. Klemberg-Sapieha, O. M. Kütell, L. Martinu and M. R. Wertheimer (Montreal, Que., Canada)

Electrical and optical properties of sprayed SnO_2 films: dependence on the oxidizing agent in the starting material 973
V. Vasu and A. Subrahmanyam (Madras, India)

Dielectric behaviour of amorphous indium oxide thin films 981
A. Balasubramanian (Pondicherry, India), M. Radhakrishnan (Coimbatore, India) and C. Balasubramanian (Annamalai Nagar, India)

Oxygen contamination of metal films produced by vacuum deposition 990
V. Grajewski, H. H. Uchida and E. Fromm (Stuttgart, F.R.G.)

Electromigration phenomena in Al–Si and Al–V–Si thin alloy films 999
P. P. J. van Engelen and A. G. Dirks (Eindhoven, The Netherlands)

C–F incorporated overlayer growth on silicon exposed to a d.c.-excited CF_4 plasma 1008
L. Lejeune, E. Collard, J. P. Grandchamp, P. Scheiblin and J. P. Gilles (Orsay, France)

Compositional and microstructural characterization of thin film lead zirconate titanate ferroelectrics 1017
M. Huffman (Colorado Springs, CO, U.S.A.), J. P. Goral, M. M. Al-Jassim, A. R. Mason and K. M. Jones (Golden, CO, U.S.A.)

Performance study of a pressure transducer with meandering-path thin film strain gauges 1023
M. M. Nayak, K. Rajanna and S. Mohan (Bangalore, India)

Planarization of dielectrics used in the manufacture of very-large-scale integrated circuits 1030
F. Malik (Rio Rancho, NM, U.S.A.) and R. Solanki (Beaverton, OR, U.S.A.)

X-ray and neutron scattering studies of laser-annealed Tb–Fe–Co thin films . 1038
P. W. Haycock, W. G. Stirling, R. D. Gould, C. C. Tang and D. L. Jones (Keele, U.K.), G. J. Herdman (Didcot, U.K.), E. W. Williams (Keele, U.K.) and K. O'Grady (Bangor, U.K.)

Preparation of Nb–Nb_2O_5–Pb alloy Josephson junctions using ion beams . . 1046
H. Mantle (Bern, Switzerland) and U. Feller (Wabern, Switzerland)

Thin film structure and adhesion of sputtered Ti–Ni layers on silicon 1056
T. Yoneyama, I. Kondo, O. Takenaka and M. Yamaoka (Aichi, Japan)

Structural and electrical properties of granular palladium cluster films 1065
A. Carl, G. Dumpich and E. F. Wassermann (Duisburg, F.R.G.)

Crystallization of amorphous $Se_{80}Te_{20}$ alloy thin films 1073
P. Lakshmi and K. S. Raghavan (Madras, India)

Characterization of low pressure deposited diamond films by X-ray photoelectron spectroscopy 1079
A. R. Chourasia and D. R. Chopra (Commerce, TX, U.S.A.), S. C. Sharma, M. Green, C. A. Dark and R. C. Hyer (Arlington, TX, U.S.A.)

AUTHOR INDEX 1087